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[Kingwan] 09/945512 **Application Number** August 30, 2001 Filing Date Forbes, Leonard **First Named Inventor Group Art Unit** 2812 Richard A. Booth **Examiner Name**

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Attorney Docket No: 01303.027US1

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(Use as many sheets as necessary) 09/945512 **Application Number** August 30, 2001 **Filing Date** Forbes, Leonard **First Named Inventor** 2812 **Group Art Unit** Richard A. Booth **Examiner Name** Attorney Docket No: 01303.027US1 Sheet 2 of 2

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